

MMBT5401LT1G, SMMBT5401LT1G, MMBT5401LT3G

High Voltage Transistor

PNP Silicon

Features

- AEC-Q101 Qualified and PPAP Capable
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	-150	Vdc
Collector - Base Voltage	V_{CBO}	-160	Vdc
Emitter - Base Voltage	V_{EBO}	-5.0	Vdc
Collector Current - Continuous	I_C	-500	mAdc

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

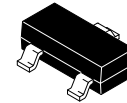
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	225	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate Above 25°C	P_D	300	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in 99.5% alumina.

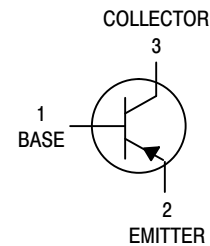


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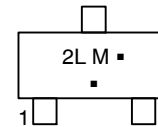
<http://onsemi.com>



SOT-23 (TO-236)
CASE 318
STYLE 6



MARKING DIAGRAM



2L = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)

*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBT5401LT1G	SOT-23 (Pb-Free)	3,000 Tape & Reel
SMMBT5401LT1G	SOT-23 (Pb-Free)	3,000 Tape & Reel
MMBT5401LT3G	SOT-23 (Pb-Free)	10,000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage (I _C = -1.0 mA _{dc} , I _B = 0)	V _{(BR)CEO}	-150	-	V _{dc}
Collector–Base Breakdown Voltage (I _C = -100 μA _{dc} , I _E = 0)	V _{(BR)CBO}	-160	-	V _{dc}
Emitter–Base Breakdown Voltage (I _E = -10 μA _{dc} , I _C = 0)	V _{(BR)EBO}	-5.0	-	V _{dc}
Collector–Base Cutoff Current (V _{CB} = -120 V _{dc} , I _E = 0) (V _{CB} = -120 V _{dc} , I _E = 0, T _A = 100°C)	I _{CBO}	-	-50 -50	nA _{dc} μA _{dc}

ON CHARACTERISTICS

DC Current Gain (I _C = -1.0 mA _{dc} , V _{CE} = -5.0 V _{dc}) (I _C = -10 mA _{dc} , V _{CE} = -5.0 V _{dc}) (I _C = -50 mA _{dc} , V _{CE} = -5.0 V _{dc})	h _{FE}	50 60 50	- 240 -	-
Collector–Emitter Saturation Voltage (I _C = -10 mA _{dc} , I _B = -1.0 mA _{dc}) (I _C = -50 mA _{dc} , I _B = -5.0 mA _{dc})	V _{CE(sat)}	- -	-0.2 -0.5	V _{dc}
Base–Emitter Saturation Voltage (I _C = -10 mA _{dc} , I _B = -1.0 mA _{dc}) (I _C = -50 mA _{dc} , I _B = -5.0 mA _{dc})	V _{BE(sat)}	- -	-1.0 -1.0	V _{dc}

SMALL-SIGNAL CHARACTERISTICS

Current–Gain — Bandwidth Product (I _C = -10 mA _{dc} , V _{CE} = -10 V _{dc} , f = 100 MHz)	f _T	100	300	MHz
Output Capacitance (V _{CB} = -10 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{obo}	-	6.0	pF
Small Signal Current Gain (I _C = -1.0 mA _{dc} , V _{CE} = -10 V _{dc} , f = 1.0 kHz)	h _{fe}	40	200	-
Noise Figure (I _C = -200 μA _{dc} , V _{CE} = -5.0 V _{dc} , R _S = 10 Ω, f = 1.0 kHz)	NF	-	8.0	dB

MMBT5401LT1G, SMMBT5401LT1G, MMBT5401LT3G

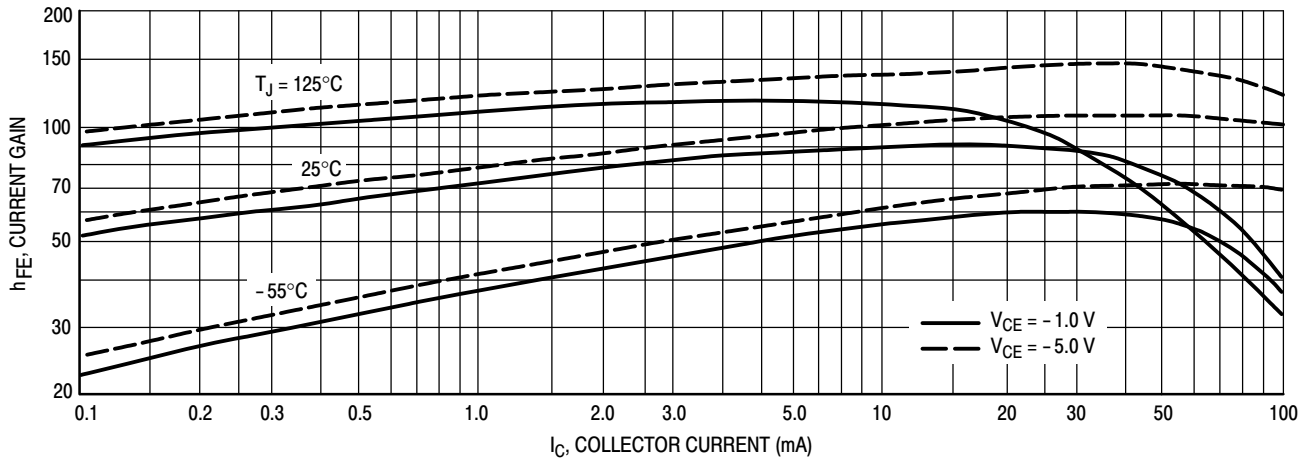


Figure 1. DC Current Gain

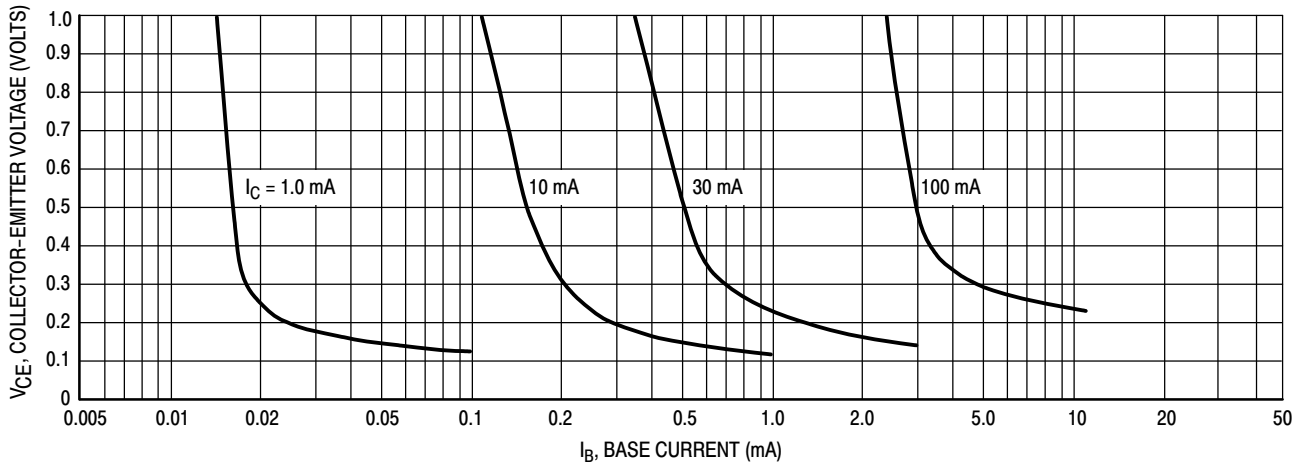


Figure 2. Collector Saturation Region

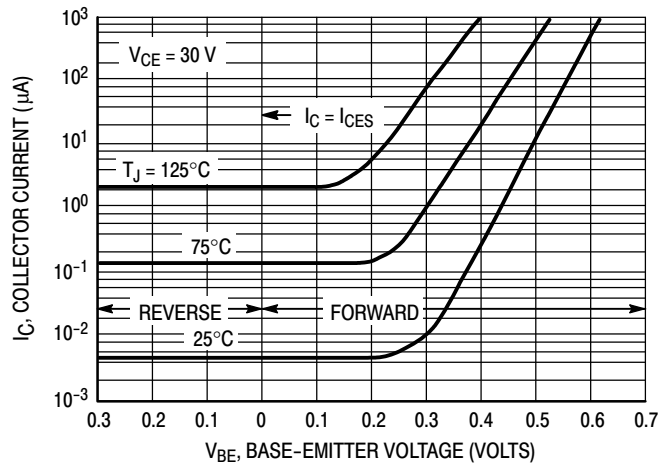


Figure 3. Collector Cut-Off Region

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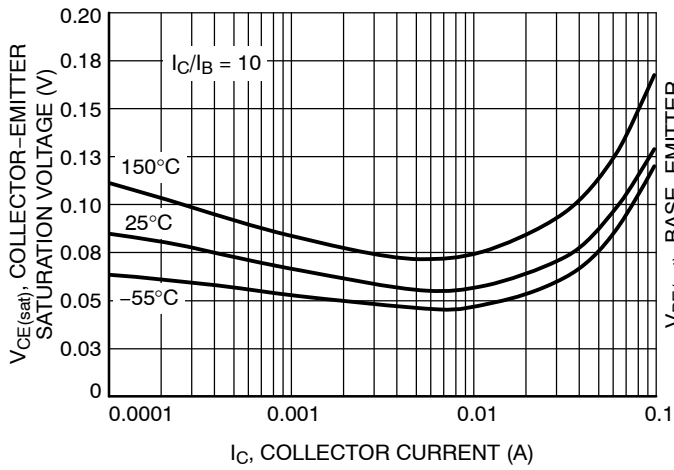


Figure 4. Collector-Emitter Saturation Voltage vs. Collector Current

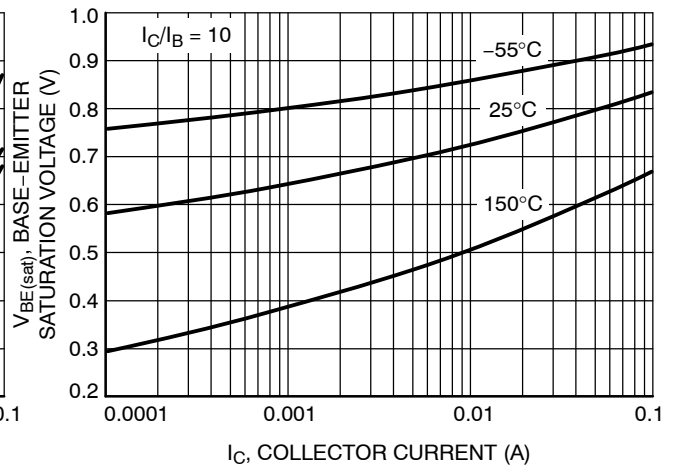


Figure 5. Base-Emitter Saturation Voltage vs. Collector Current

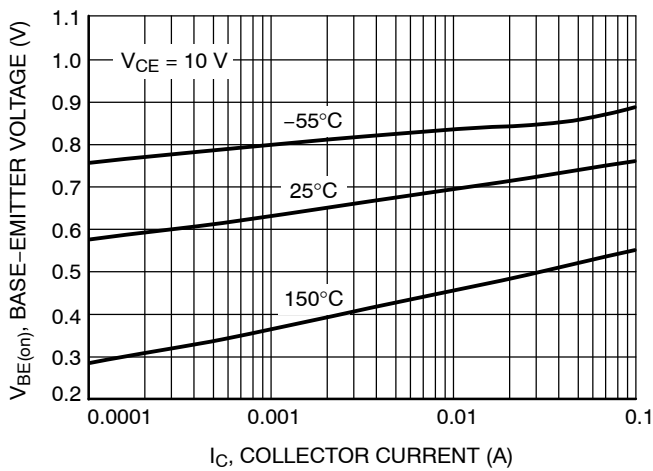


Figure 6. Base-Emitter Voltage vs. Collector Current

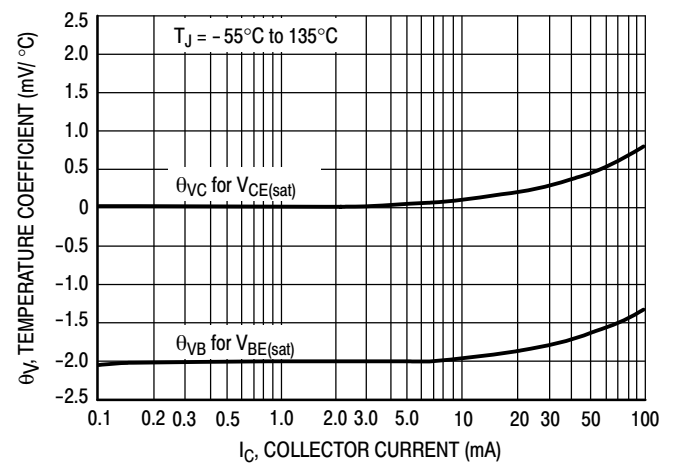
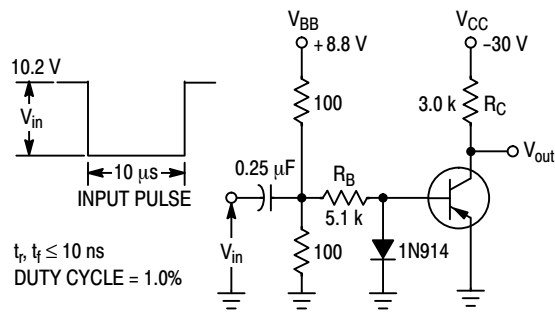


Figure 7. Temperature Coefficients



Values Shown are for $I_C @ 10 \text{ mA}$

Figure 8. Switching Time Test Circuit

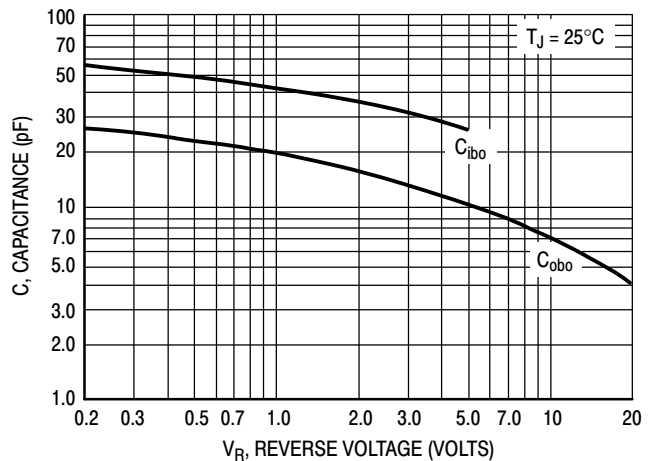


Figure 9. Capacitances

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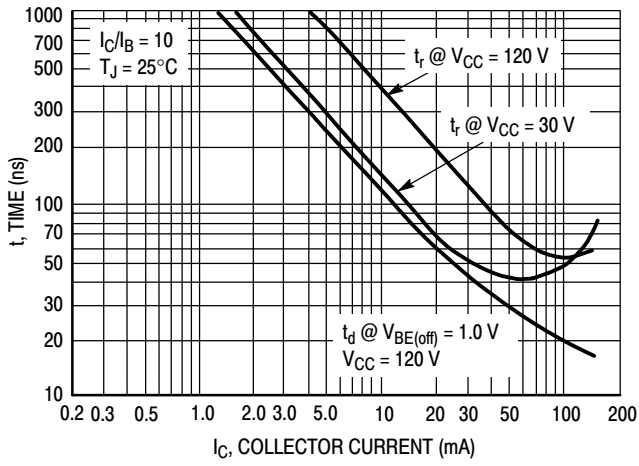


Figure 10. Turn-On Time

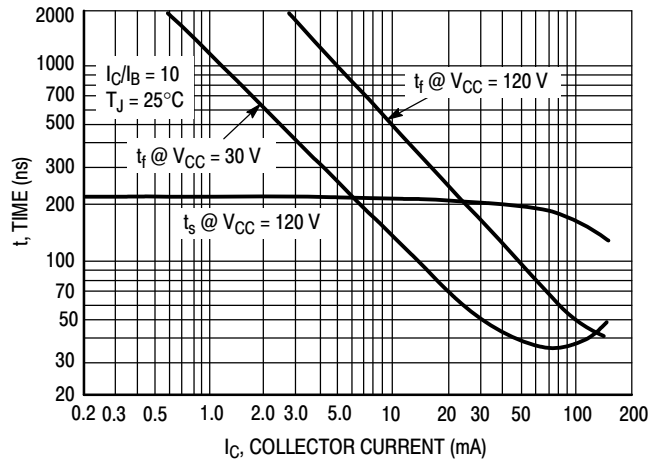


Figure 11. Turn-Off Time

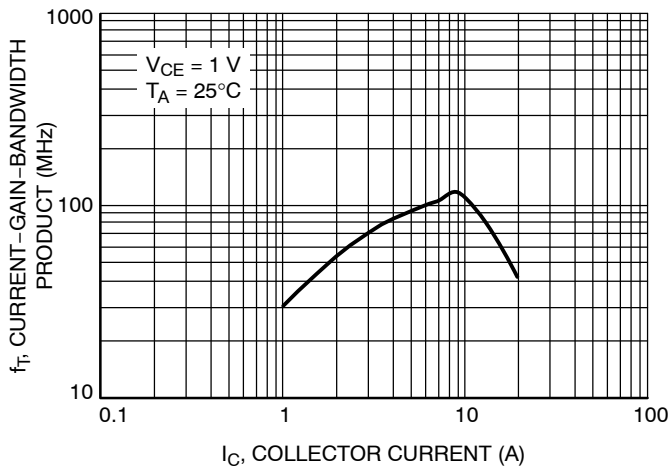


Figure 12. Current Gain Bandwidth Product

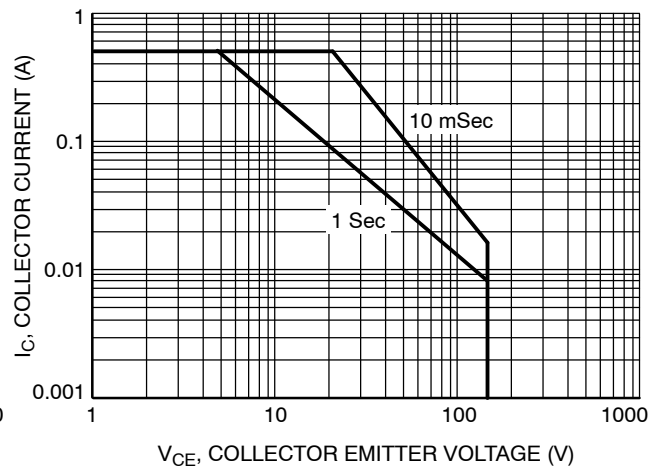
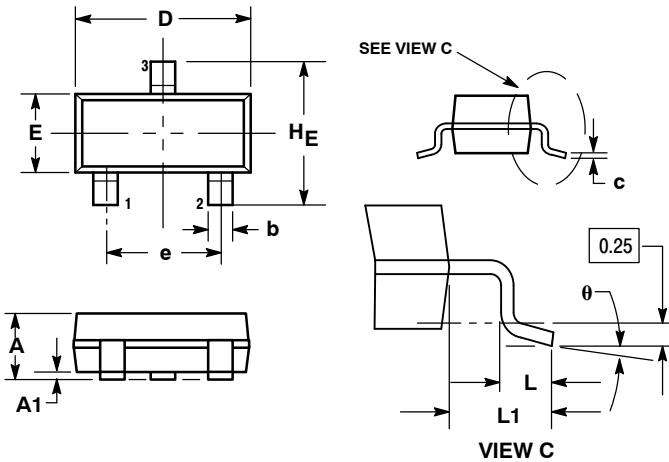


Figure 13. Safe Operating Area

MMBT5401LT1G, SMMBT5401LT1G, MMBT5401LT3G

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AP



NOTES:

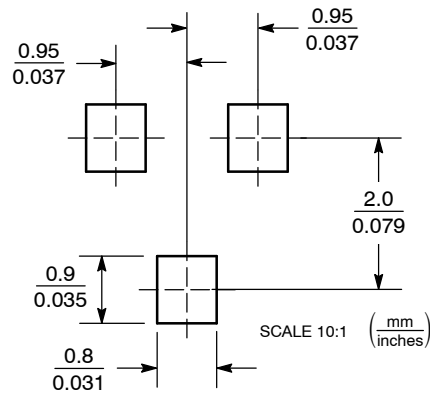
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT



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